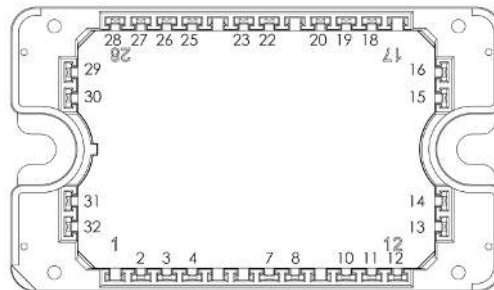
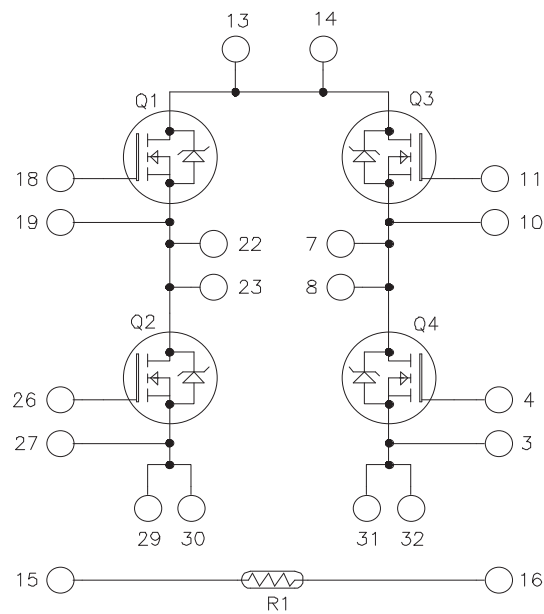


## Full Bridge SiC MOSFET Power Module

### Product Overview

The MSCSM70HM19T3AG device is a full bridge 700V, 124A silicon carbide (SiC) power module.



**Notes:**

- All multiple inputs and outputs must be shorted together. Example: 13/14, 29/30, 22/23, and so on.
- All ratings at  $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise specified.



These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

## Features

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The following are key features of the MSCSM70HM19T3AG device:

- SiC Power MOSFET
  - High speed switching
  - Low  $R_{DS(on)}$
  - Ultra low loss
- Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring
- Aluminum Nitride (AlN) substrate for improved thermal performance

## Benefits

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The following are the benefits of MSCSM70HM19T3AG device:

- High efficiency converter
- Outstanding performance at high frequency operation
- Solderable terminals both for power and signal for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Low profile
- RoHS compliant

## Application

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The MSCSM70HM19T3AG device is designed for the following applications:

- Welding converters
- Switched mode power supplies
- Uninterruptible power supplies
- EV motor and traction drive

## 1. Electrical Specifications

This section provides the electrical specifications of the MSCSM70HM19T3AG device.

### 1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM70HM19T3AG device.

**Table 1-1. Absolute Maximum Ratings**

| Symbol       | Parameter                  | Maximum Ratings                  | Unit             |
|--------------|----------------------------|----------------------------------|------------------|
| $V_{DSS}$    | Drain-Source voltage       | 700                              | V                |
| $I_D$        | Continuous drain current   | $T_C = 25\text{ }^\circ\text{C}$ | 124 <sup>1</sup> |
|              |                            | $T_C = 80\text{ }^\circ\text{C}$ | 98 <sup>1</sup>  |
| $I_{DM}$     | Pulsed drain current       | 250                              |                  |
| $V_{GS}$     | Gate-Source voltage        | -10/23                           | V                |
| $R_{DS(on)}$ | Drain-Source ON resistance | 19                               | m $\Omega$       |
| $P_D$        | Power dissipation          | $T_C = 25\text{ }^\circ\text{C}$ | 365              |

**Note:**

1. Specification of SiC MOSFET device but output current must be limited due to size of power connectors.

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM70HM19T3AG device.

**Table 1-2. Electrical Characteristics**

| Symbol       | Characteristic                  | Test Conditions                          | Min.                              | Typ. | Max. | Unit          |            |
|--------------|---------------------------------|--|-----------------------------------|------|------|---------------|------------|
| $I_{DSS}$    | Zero gate voltage drain current | $V_{GS} = 0V$<br>$V_{DS} = 700V$         | —                                 | —    | 100  | $\mu\text{A}$ |            |
| $R_{DS(on)}$ | Drain-Source on resistance      | $V_{GS} = 20V$<br>$I_D = 40A$            | $T_J = 25\text{ }^\circ\text{C}$  | —    | 15   | 19            | m $\Omega$ |
|              |                                 |  | $T_J = 175\text{ }^\circ\text{C}$ | —    | 18.8 | —             |            |
| $V_{GS(th)}$ | Gate threshold voltage          | $V_{GS} = V_{DS}$<br>$I_D = 4\text{ mA}$ | 1.9                               | 2.4  | —    | V             |            |
| $I_{GSS}$    | Gate-Source leakage current     | $V_{GS} = 20V; V_{DS} = 0V$              | —                                 | —    | 150  | nA            |            |

# MSCSM70HM19T3AG

## Electrical Specifications

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM70HM19T3AG device.

**Table 1-3. Dynamic Characteristics**

| Symbol       | Characteristic                      | Test Conditions   | Min.                      | Typ. | Max. | Unit               |               |
|--------------|-------------------------------------|---|---------------------------|------|------|--------------------|---------------|
| $C_{iss}$    | Input capacitance                   | $V_{GS} = 0V$   | —                         | 4500 | —    | pF                 |               |
| $C_{oss}$    | Output capacitance                  | $V_{DS} = 700V$   | —                         | 510  | —    |                    |               |
| $C_{rss}$    | Reverse transfer capacitance        | $f = 1\text{ MHz}$  | —                         | 29   | —    |                    |               |
| $Q_g$        | Total gate charge                   | $V_{GS} = -5V/20V$  | —                         | 215  | —    | nC                 |               |
| $Q_{gs}$     | Gate-Source charge                  | $V_{Bus} = 470V$  | —                         | 58   | —    |                    |               |
| $Q_{gd}$     | Gate-Drain charge                   | $I_D = 40A$   | —                         | 35   | —    |                    |               |
| $T_{d(on)}$  | Turn-on delay time                  | $V_{GS} = -5V/20V$  | $T_J = 150^\circ\text{C}$ | —    | 40   | —                  | ns            |
| $T_r$        | Rise time                           | $V_{Bus} = 400V$  |                           | —    | 40   | —                  |               |
| $T_{d(off)}$ | Turn-off delay time                 | $I_D = 80A$   |                           | —    | 50   | —                  |               |
| $T_f$        | Fall time                           | $R_{G(on)} = 68\Omega$<br>$R_{G(off)} = 4.7\Omega$                                    |                           | —    | 20   | —                  |               |
| $E_{on}$     | Turn-on energy                      | $V_{GS} = -5V/20V$  | $T_J = 150^\circ\text{C}$ | —    | 893  | —                  | $\mu\text{J}$ |
| $E_{off}$    | Turn-off energy                     | $V_{Bus} = 400V$<br>$I_D = 80A$<br>$R_{G(on)} = 68\Omega$<br>$R_{G(off)} = 4.7\Omega$ | $T_J = 150^\circ\text{C}$ | —    | 194  | —                  |               |
| $R_{Gint}$   | Internal gate resistance            |   | —                         | 0.69 | —    | $\Omega$           |               |
| $R_{thJC}$   | Junction-to-case thermal resistance |   | —                         | —    | 0.41 | $^\circ\text{C/W}$ |               |

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM70HM19T3AG device.

**Table 1-4. Body Diode Ratings and Characteristics**

| Symbol   | Characteristic           | Test Conditions                                   | Min. | Typ. | Max. | Unit |
|----------|--------------------------|---|------|------|------|------|
| $V_{SD}$ | Diode forward voltage    | $V_{GS} = 0V; I_{SD} = 40A$                       | —    | 3.4  | —    | V    |
|          |                          | $V_{GS} = -5V; I_{SD} = 40A$                      | —    | 3.8  | —    |      |
| $t_{rr}$ | Reverse recovery time    | $I_{SD} = 40A; V_{GS} = -5V$                      | —    | 38   | —    | ns   |
| $Q_{rr}$ | Reverse recovery charge  | $V_R = 400V; di_F/dt = 1000\text{ A}/\mu\text{s}$ | —    | 318  | —    | nC   |
| $I_{rr}$ | Reverse recovery current |   | —    | 14.8 | —    | A    |

### 1.2 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM70HM19T3AG device.

**Table 1-5. Thermal and Package Characteristics**

| Symbol            | Characteristics  | Min.        | Max.                  | Unit |   |     |
|-------------------|--|-------------|-----------------------|------|---|-----|
| V <sub>ISOL</sub> | RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz | 4000        | —                     | V    |   |     |
| T <sub>J</sub>    | Operating junction temperature range                               | −40         | 175                   | °C   |   |     |
| T <sub>JOP</sub>  | Recommended junction temperature under switching conditions        | −40         | T <sub>Jmax</sub> −25 |      |   |     |
| T <sub>STG</sub>  | Storage temperature range  | −40         | 125                   |      |   |     |
| T <sub>C</sub>    | Operating case temperature   | −40         | 125                   |      |   |     |
| Torque            | Mounting torque  | To heatsink | M4                    | 2    | 3 | N.m |
| Wt                | Package weight   | —           | 110                   |      |   | g   |

The following table lists the temperature sensor NTC of the MSCSM70HM19T3AG device.

**Table 1-6. Temperature Sensor NTC**

| Symbol                            | Characteristic             | Min.                    | Typ. | Max. | Unit |
|-----------------------------------|----------------------------|-------------------------|------|------|------|
| R <sub>25</sub>                   | Resistance at 25°C         | —                       | 50   | —    | kΩ   |
| ΔR <sub>25</sub> /R <sub>25</sub> | —                          | —                       | 5    | —    | %    |
| B <sub>25/85</sub>                | T <sub>25</sub> = 298.15 K | —                       | 3952 | —    | K    |
| ΔB/B                              | —                          | T <sub>C</sub> = 100 °C | 4    | —    | %    |

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right]}$$

T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

**Note:** See [APT0406—Using NTC Temperature Sensor Integrated into Power Module](#) for more information.

### 1.3 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM70HM19T3AG device.

Figure 1-1. Maximum Thermal Impedance

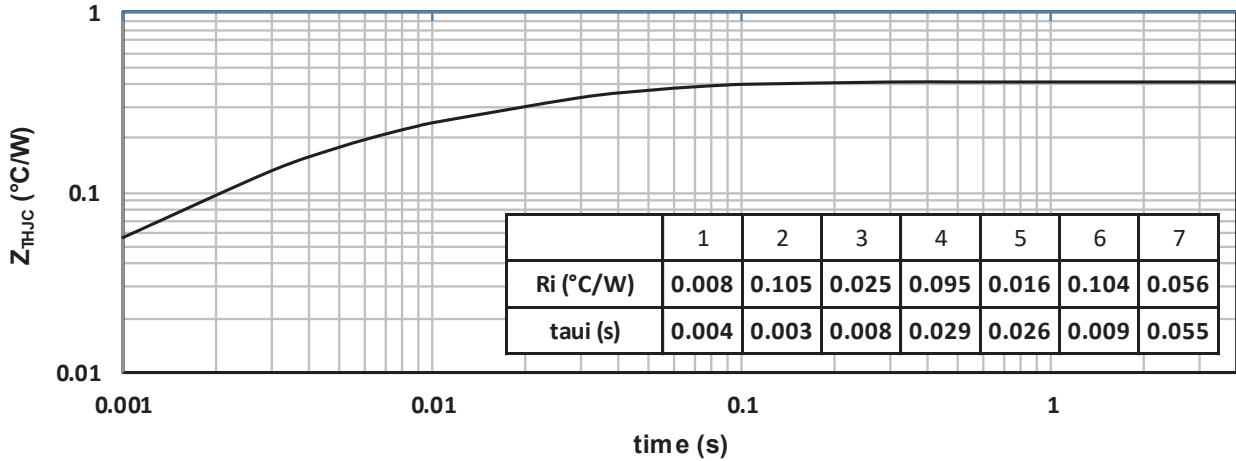


Figure 1-2. Output Characteristics,  $T_J = 25^\circ\text{C}$

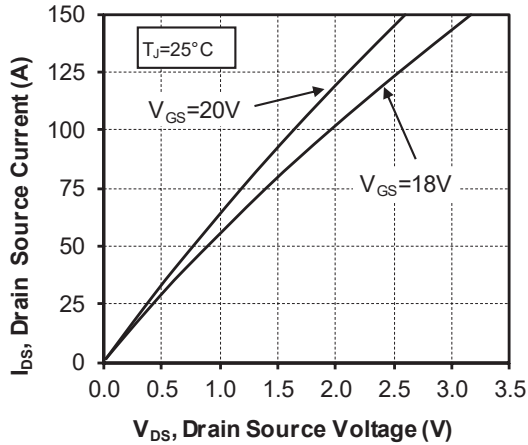


Figure 1-3. Output Characteristics,  $T_J = 175^\circ\text{C}$

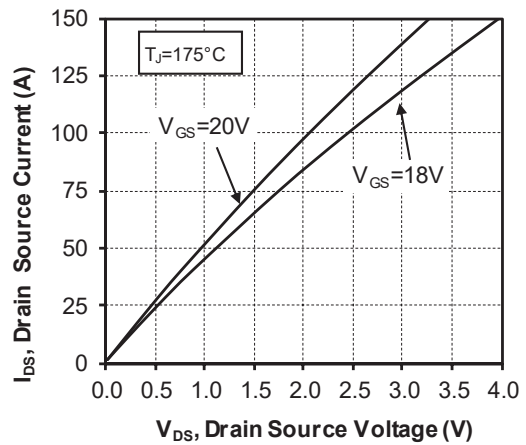


Figure 1-4. Normalized  $R_{DS(on)}$  vs. Temperature

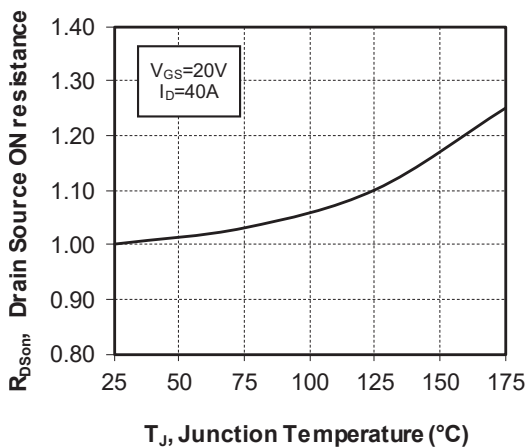


Figure 1-5. Transfer Characteristics

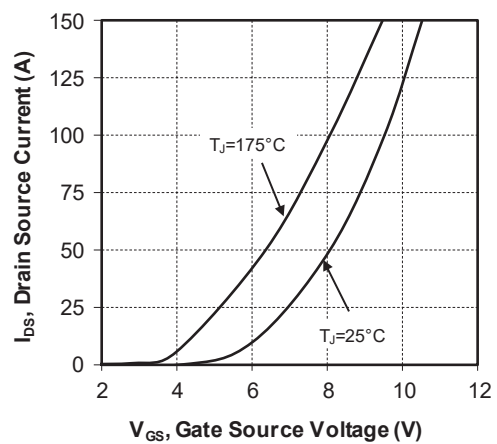


Figure 1-6. Switching Energy vs. Current

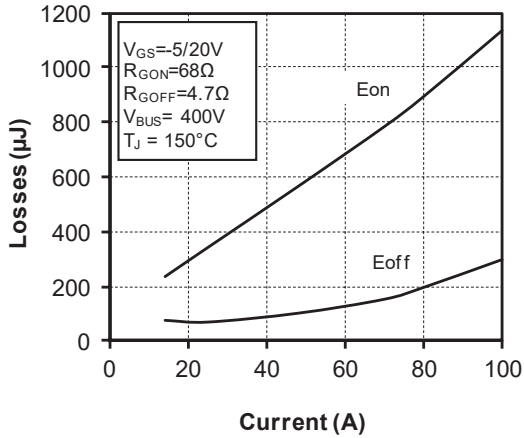


Figure 1-7. Turn On Energy vs.  $R_g$

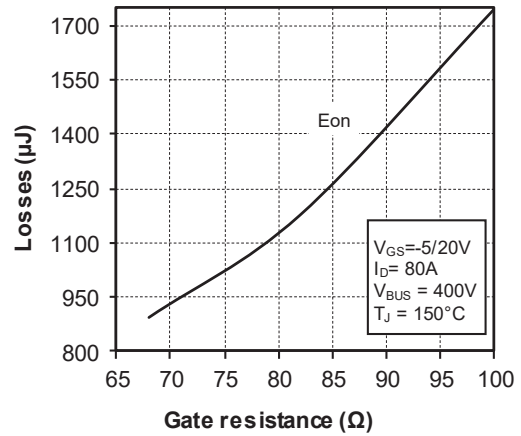


Figure 1-8. Capacitance vs. Drain Source Voltage

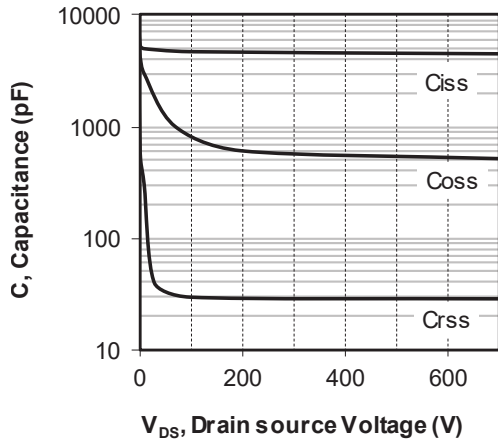


Figure 1-9. Gate Charge vs. Gate Source Voltage

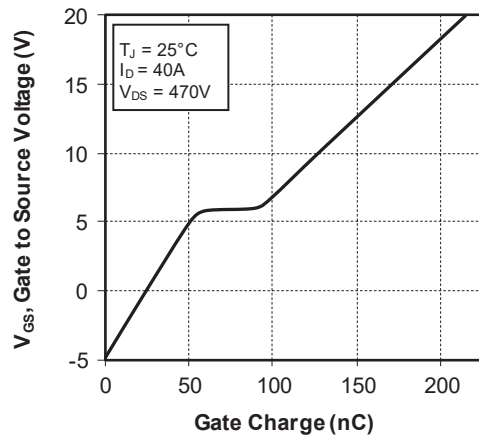


Figure 1-10. Body Diode Characteristics,  $T_J = 25^\circ\text{C}$

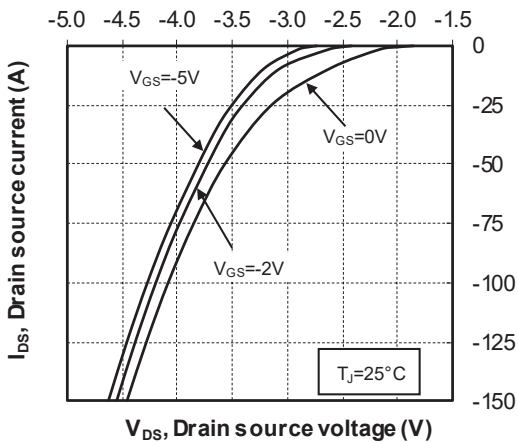


Figure 1-11. 3<sup>rd</sup> Quadrant Characteristics,  $T_J = 25^\circ\text{C}$

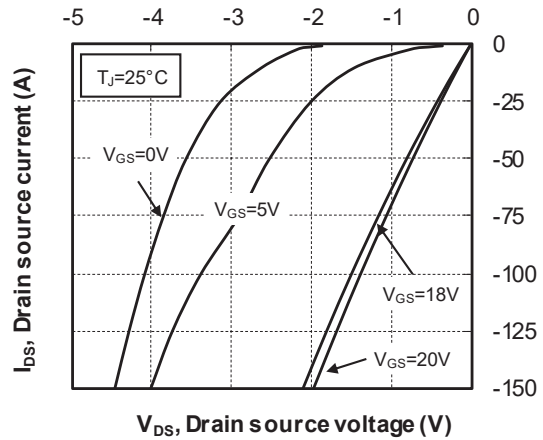


Figure 1-12. Body Diode Characteristics,  $T_J = 175^\circ\text{C}$

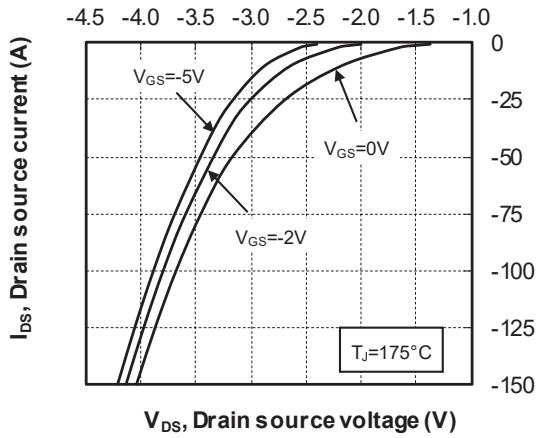


Figure 1-13. 3<sup>rd</sup> Quadrant Characteristics,  $T_J = 175^\circ\text{C}$

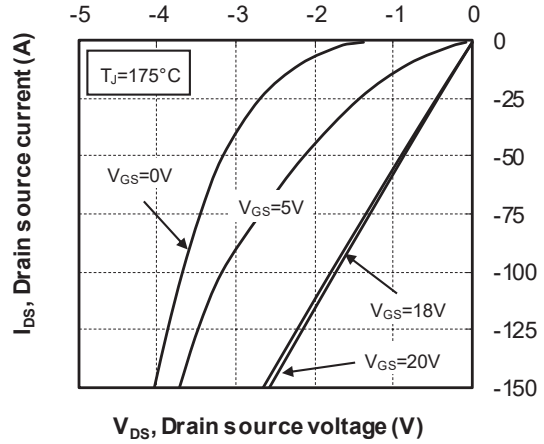


Figure 1-14. Operating Frequency vs Drain Current

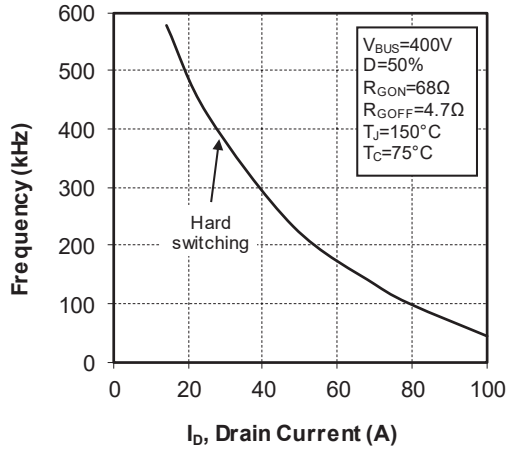
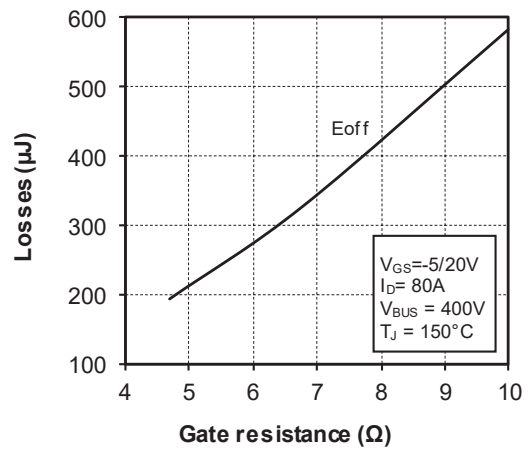


Figure 1-15. Turn Off Energy vs. Rg





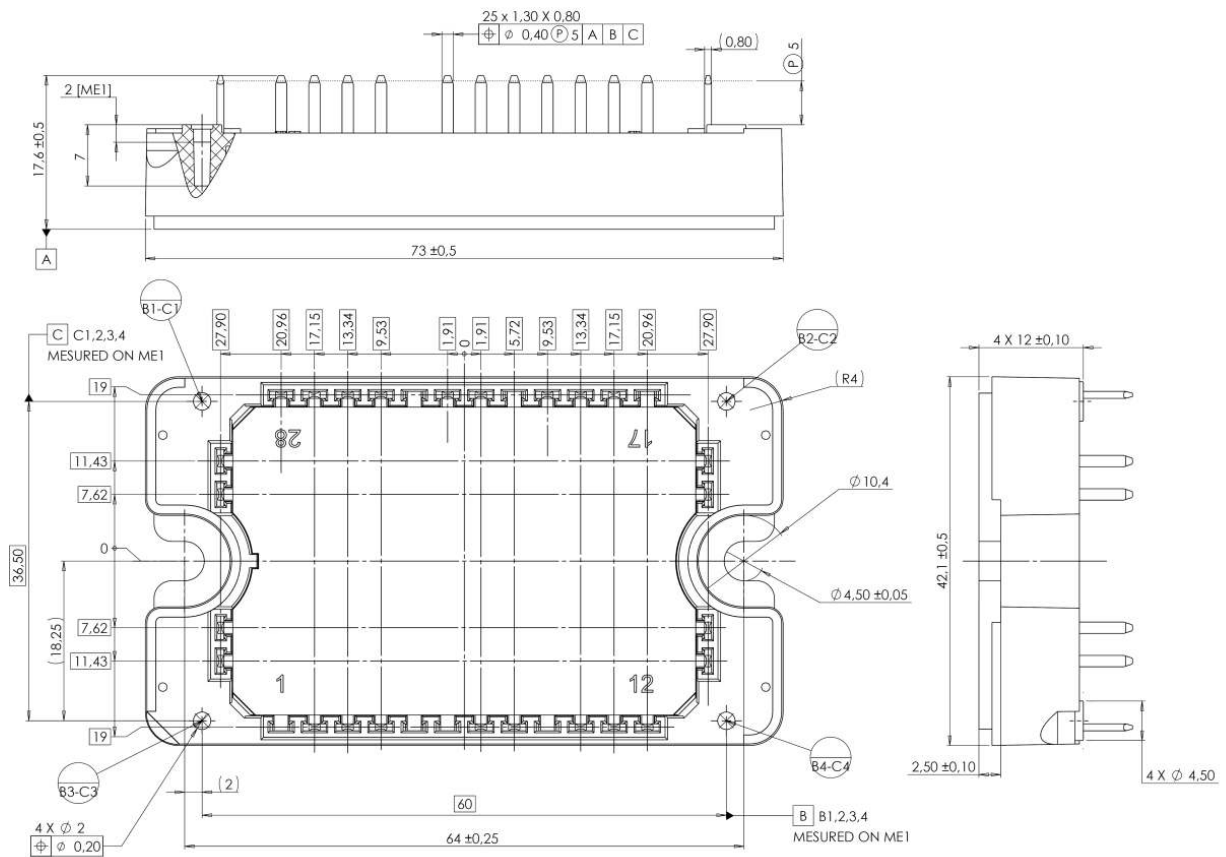
## 2. Package Specifications

The following section shows the package specification of the MSCSM70HM19T3AG device.

### 2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM70HM19T3AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



**Note:** See [AN3500A—Mounting Instructions for SP1F and SP3F Power Modules](#) for more information.

**3. Revision History**

| Revision | Date    | Description     |
|----------|---------|-----------------|
| A        | 06/2022 | Initial Release |

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